

FDPF7N50U / FDPF7N50U_G

N-Channel UniFET™ Ultra FRFET™ MOSFET

500 V, 5 A, 1.5 Ω

Features

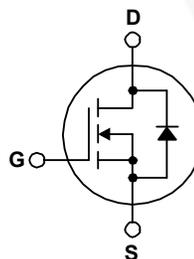
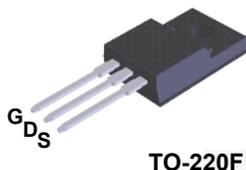
- $R_{DS(on)} = 1.5 \Omega$ (Max.) @ $V_{GS} = 10 V$, $I_D = 2.5 A$
- Low Gate Charge (Typ. 12.8 nC)
- Low C_{rss} (Typ. 9 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability

Applications

- LCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. UniFET Ultra FRFET™ MOSFET has much superior body diode reverse recovery performance. Its t_{rr} is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FDPF7N50U / FDPF7N50U_G	Unit
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ C$)	5*
		- Continuous ($T_C = 100^\circ C$)	3*
I_{DM}	Drain Current	- Pulsed (Note 1)	20*
V_{GSS}	Gate-Source voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	125	mJ
I_{AR}	Avalanche Current (Note 1)	5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	8.9	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	20	V/ns
P_D	Power Dissipation	($T_C = 25^\circ C$)	31.3
		- Derate above $25^\circ C$	0.25
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ C$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDPF7N50U / FDPF7N50U_G	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.0	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF7N50U	FDPF7N50U	TO-220F	Tube	N/A	N/A	50 units
FDPF7N50U_G	FDPF7N50U	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V V _{DS} = 400 V, T _C = 125°C	--	--	25 250	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.5 A	--	1.2	1.5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.5 A	--	2.5	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	720	940	pF
C _{oss}	Output Capacitance		--	95	190	pF
C _{rss}	Reverse Transfer Capacitance		--	9	13.5	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 5 A R _G = 25 Ω (Note 4)	--	6	20	ns
t _r	Turn-On Rise Time		--	55	120	ns
t _{d(off)}	Turn-Off Delay Time		--	25	60	ns
t _f	Turn-Off Fall Time		--	35	80	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 5 A V _{GS} = 10 V (Note 4)	--	12.8	16.6	nC
Q _{gs}	Gate-Source Charge		--	3.7	--	nC
Q _{gd}	Gate-Drain Charge		--	5.8	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	20	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 5 A	--	--	1.6	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 5 A di _F /dt = 100 A/μs	--	40	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.04	--	μC

NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 10 mH, I_{AS} = 5 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

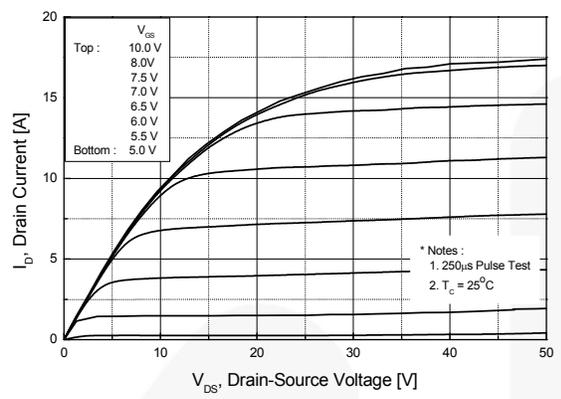


Figure 2. Transfer Characteristics

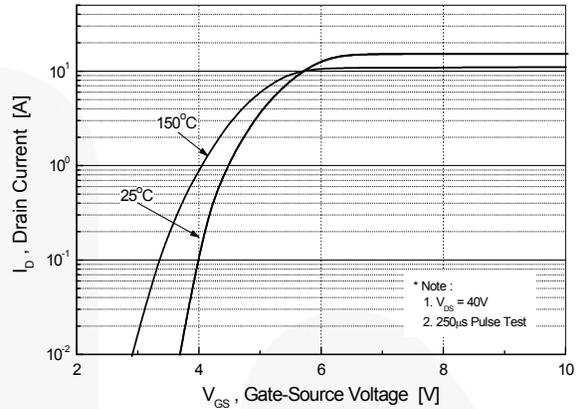


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

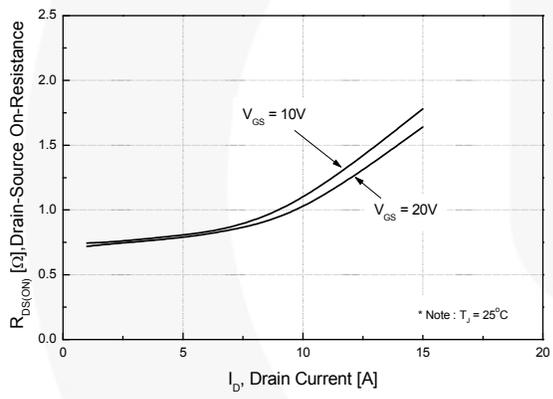


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

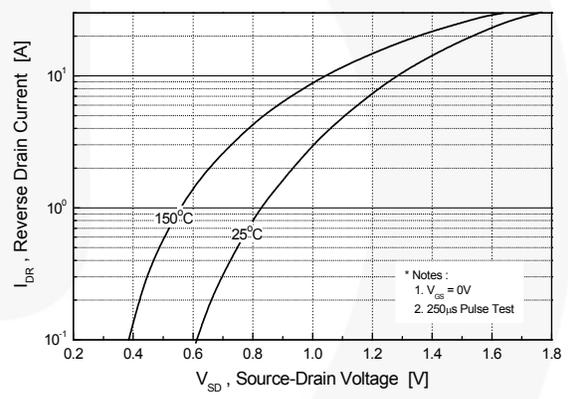


Figure 5. Capacitance Characteristics

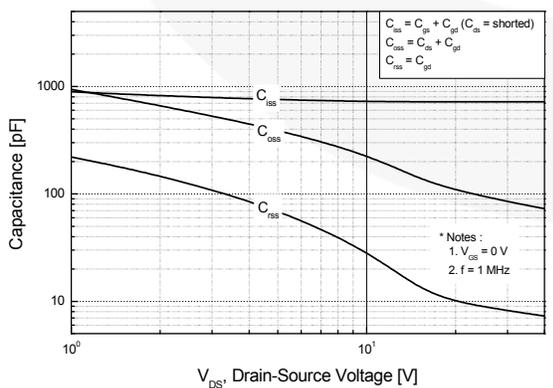
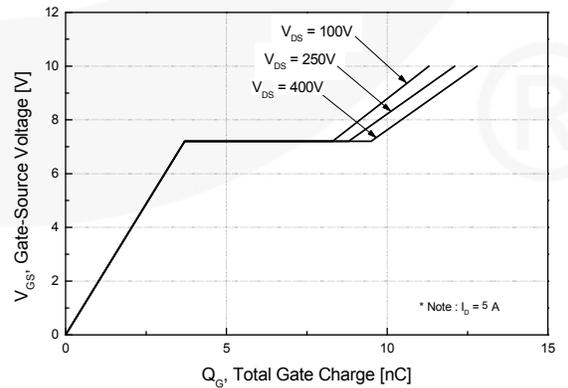


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

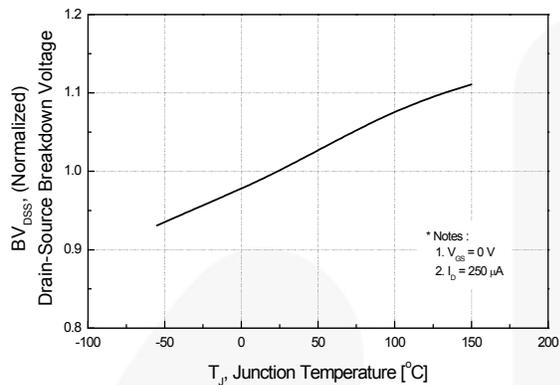


Figure 8. Maximum Drain Current Vs. Case Temperature

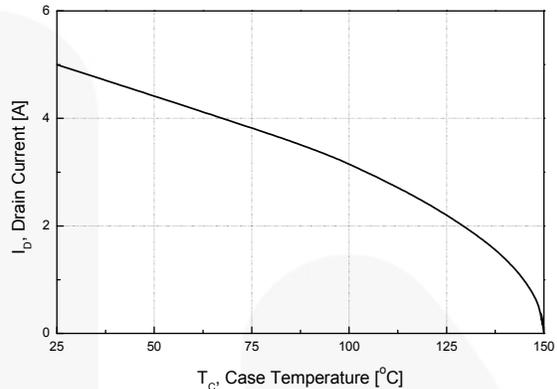


Figure 9. Maximum Safe Operating Area

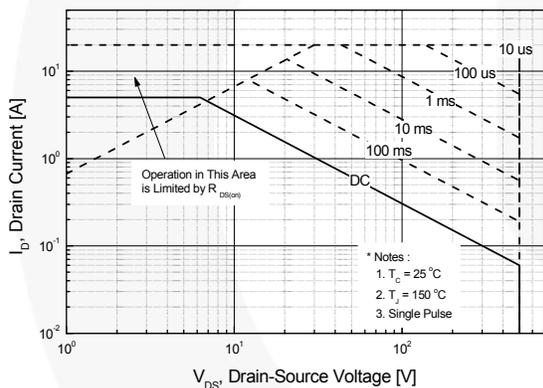
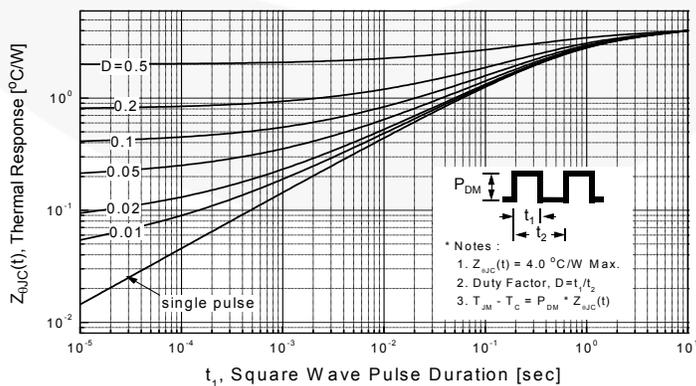


Figure 10. Transient Thermal Response Curve



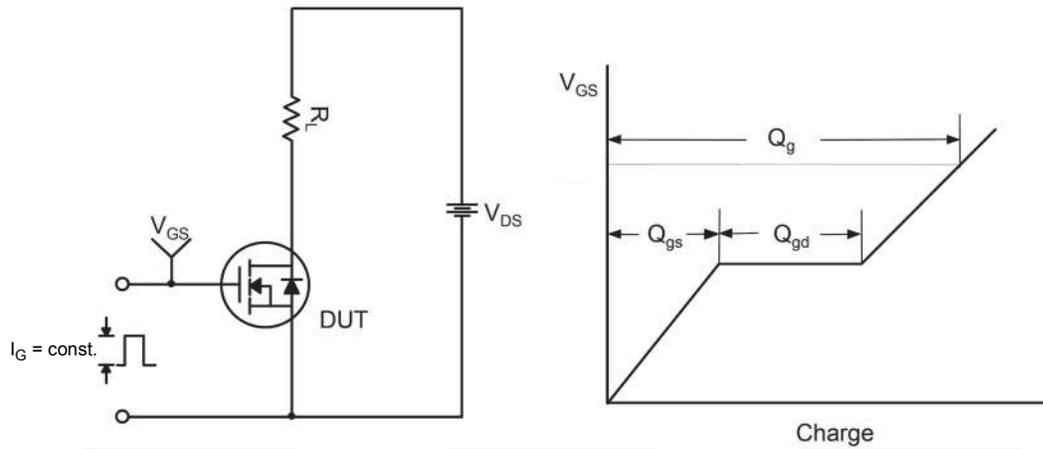


Figure 11. Gate Charge Test Circuit & Waveform

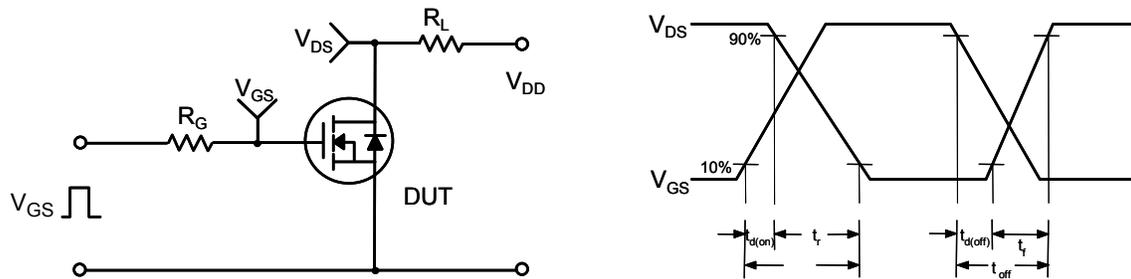


Figure 12. Resistive Switching Test Circuit & Waveforms

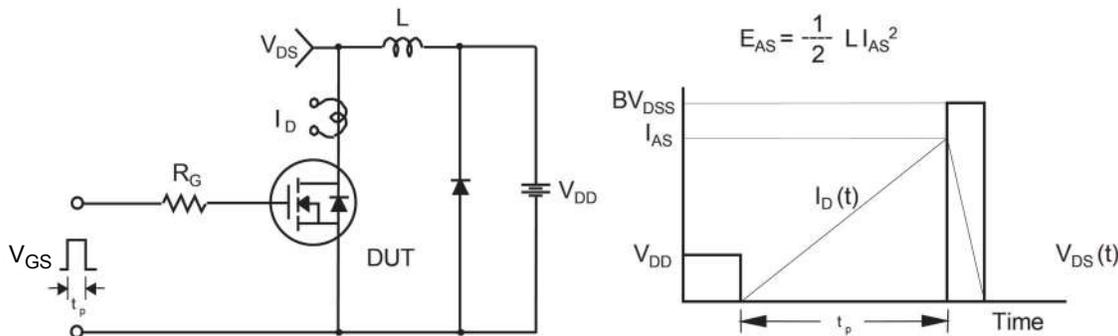


Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms

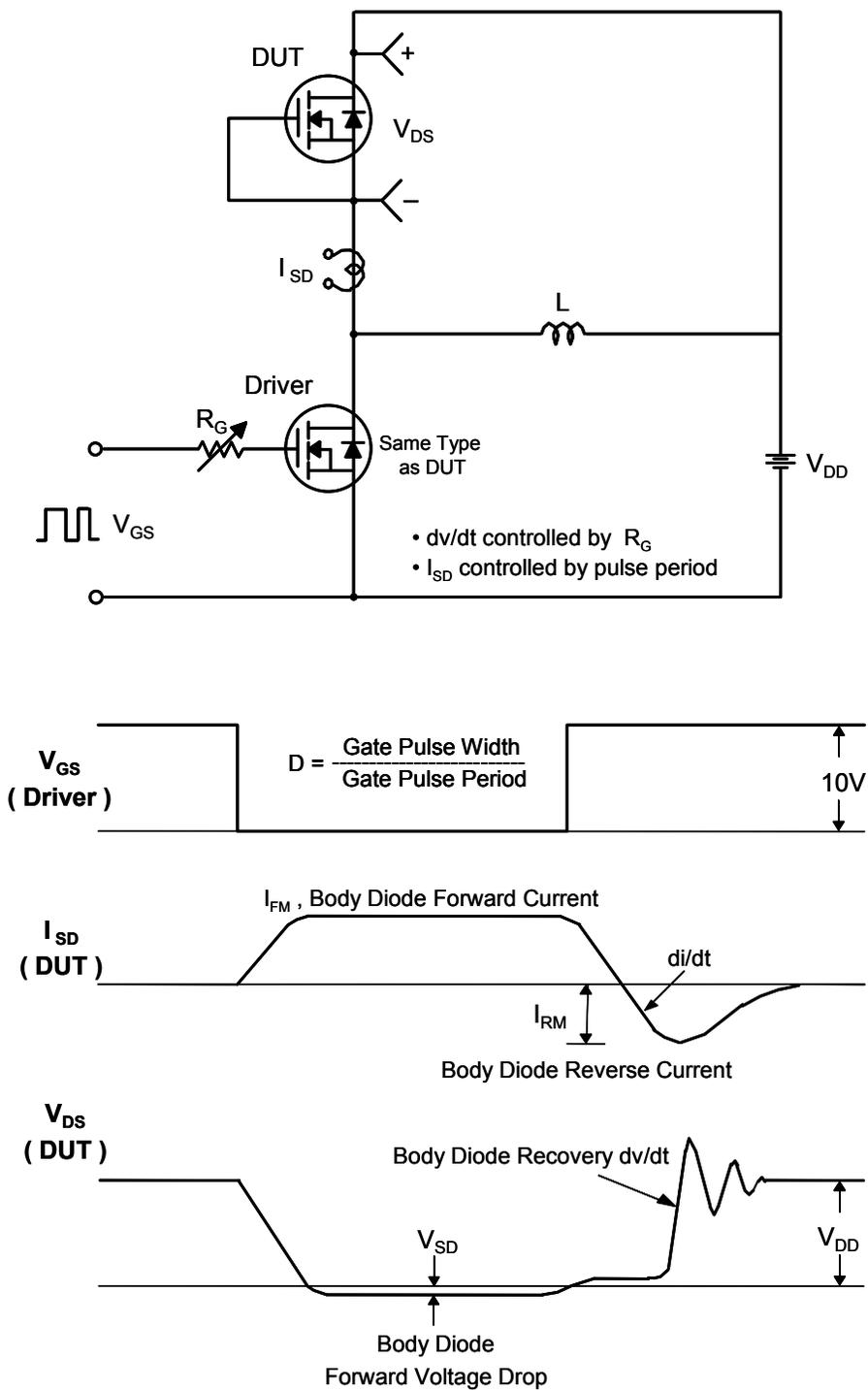


Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

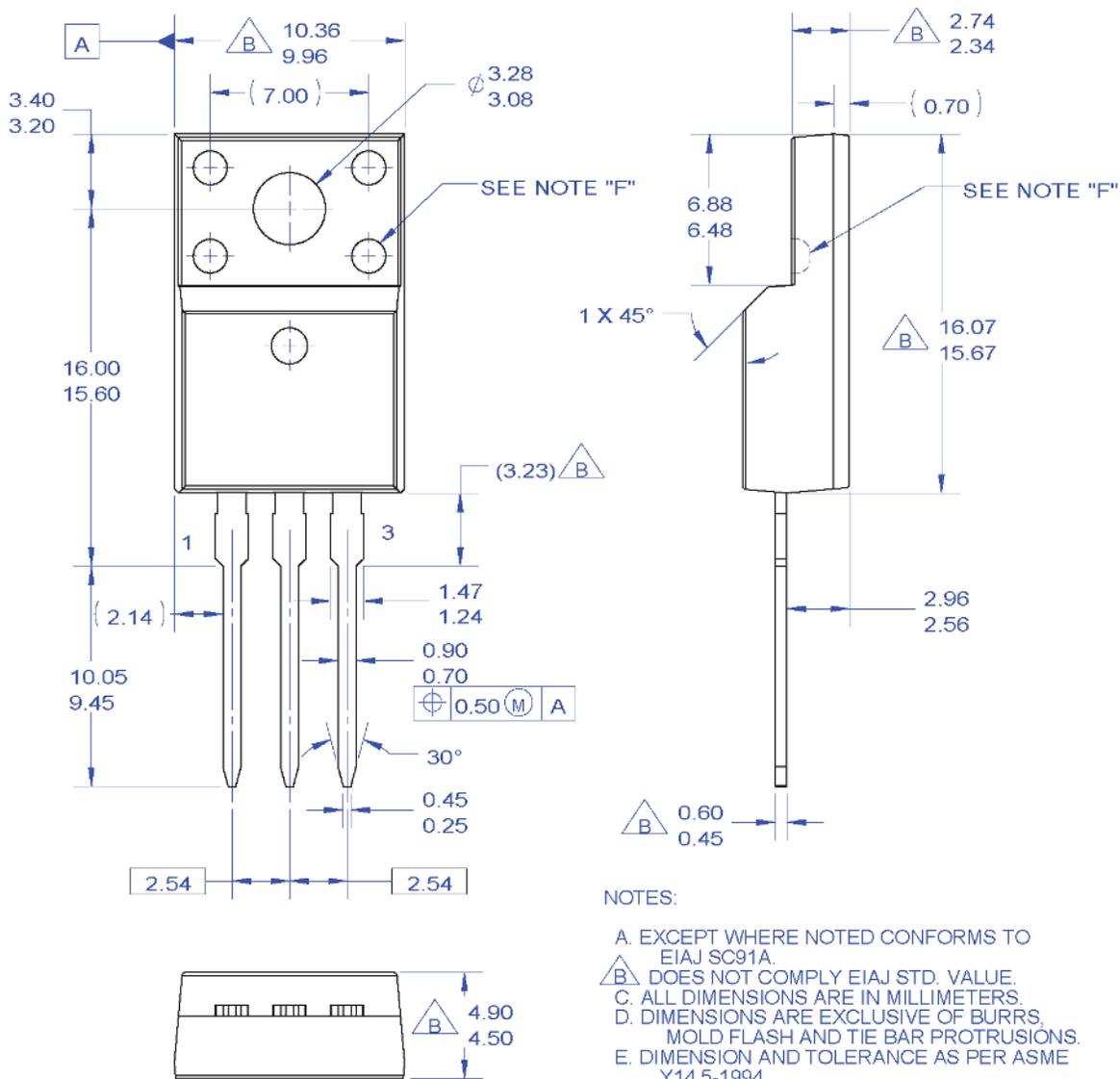


Figure 15. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-003

